

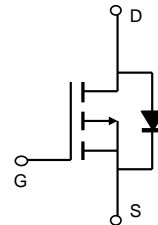
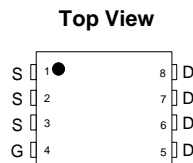
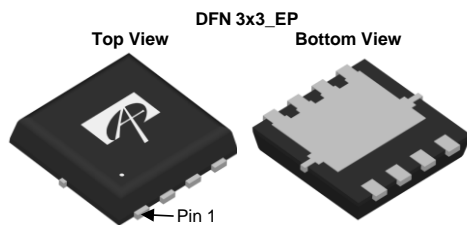
General Description

The AON7401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

Product Summary

V_{DS}	-30V
I_D (at $V_{GS}=-10V$)	-35A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	< 14m Ω
$R_{DS(ON)}$ (at $V_{GS}=-6V$)	< 17m Ω

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	-35
		$T_C=100^\circ\text{C}$	-23
Pulsed Drain Current ^C	I_{DM}	-80	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	-12
		$T_A=70^\circ\text{C}$	-9.7
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	29
		$T_C=100^\circ\text{C}$	12
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	30	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}		60	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead	$R_{\theta JL}$	3.5	4.2	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±25V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1.7	-2.2	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-80			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-9A T _J =125°C		11 16	14 19	mΩ
		V _{GS} =-6V, I _D =-7A		12.9	17	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-9A		27		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Maximum Body-Diode Continuous Current				-25	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		2060	2600	pF
C _{oss}	Output Capacitance			370		pF
C _{riss}	Reverse Transfer Capacitance			295		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.4	3.6	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-9A		30	39	nC
Q _{gs}	Gate Source Charge			4.6		nC
Q _{gd}	Gate Drain Charge			10		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =1.6Ω, R _{GEN} =3Ω		11		ns
t _r	Turn-On Rise Time			9.4		ns
t _{D(off)}	Turn-Off DelayTime			24		ns
t _f	Turn-Off Fall Time			12		ns
t _{rr}	Body Diode Reverse Recovery Time		I _F =-9A, di/dt=500A/μs		14	18
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-9A, di/dt=500A/μs		35		nC

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t ≤ 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150° C may be used if the PCB allows it.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsirk, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

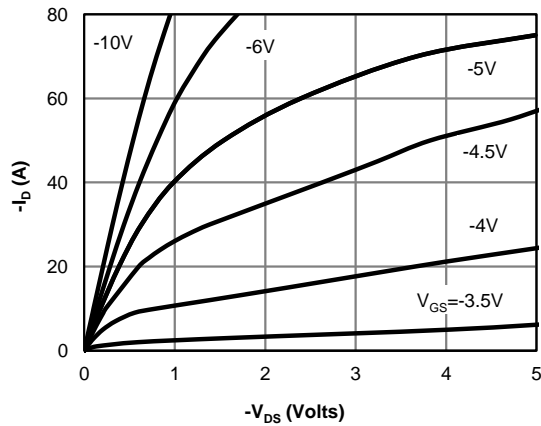


Fig 1: On-Region Characteristics (Note E)

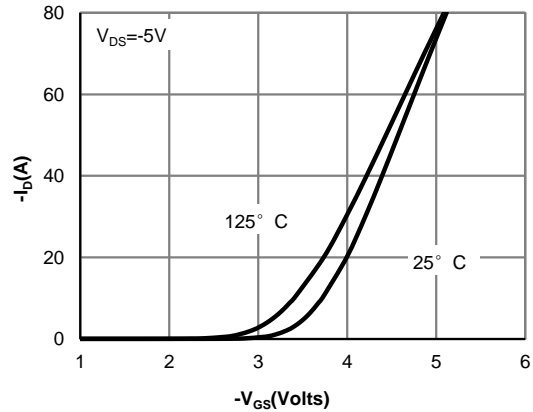


Figure 2: Transfer Characteristics (Note E)

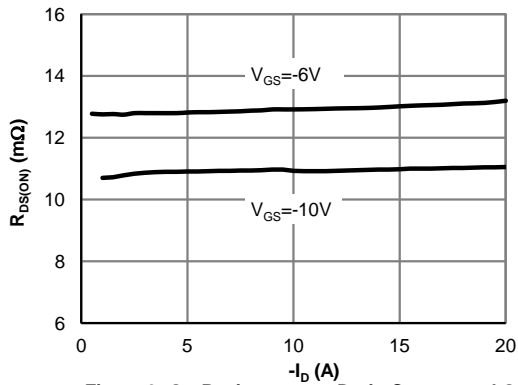


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

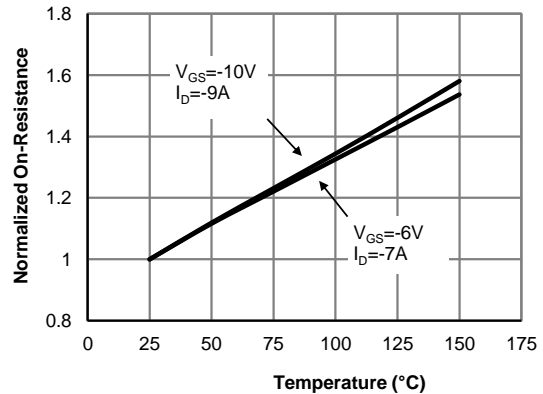


Figure 4: On-Resistance vs. Junction Temperature (Note E)

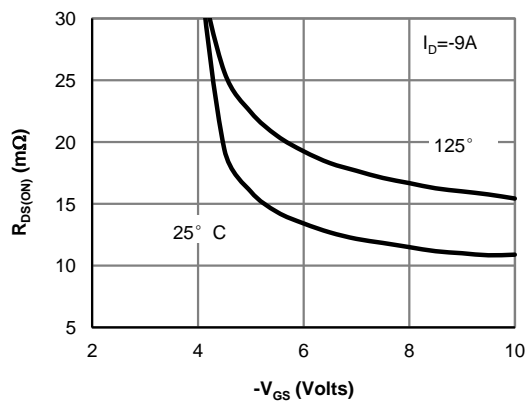


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

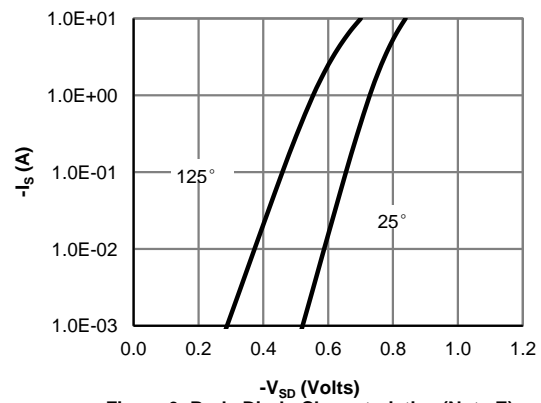


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

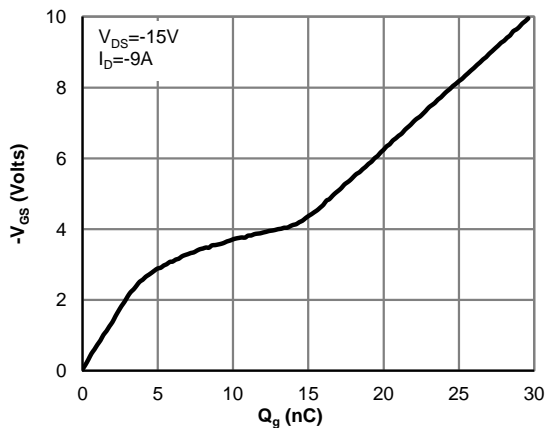


Figure 7: Gate-Charge Characteristics

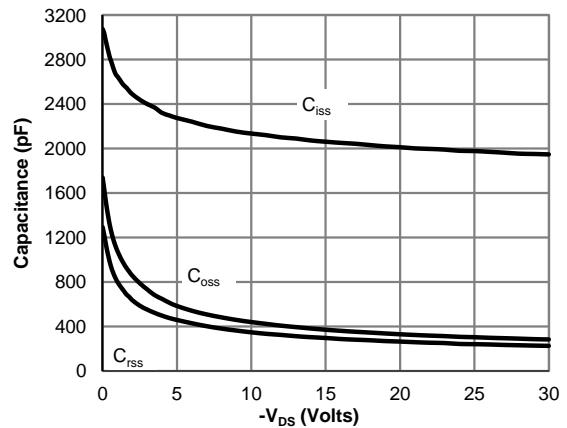


Figure 8: Capacitance Characteristics

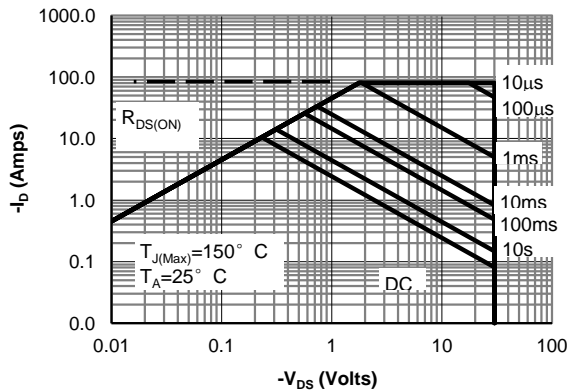


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

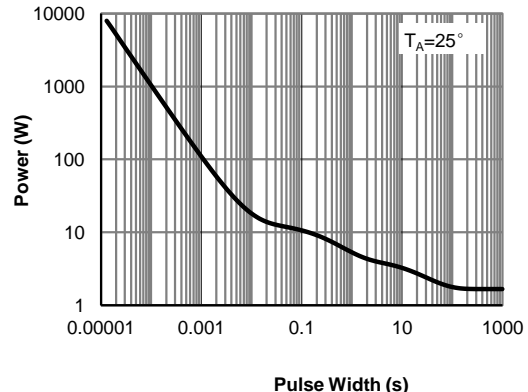


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

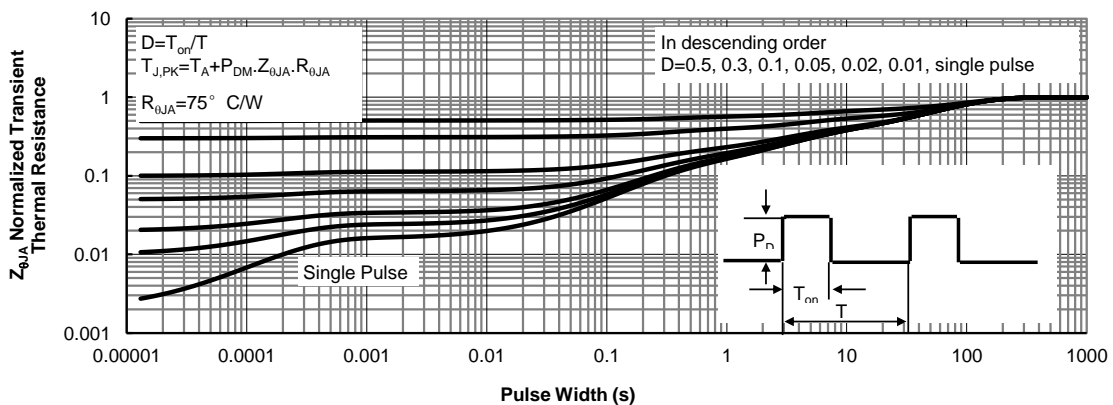
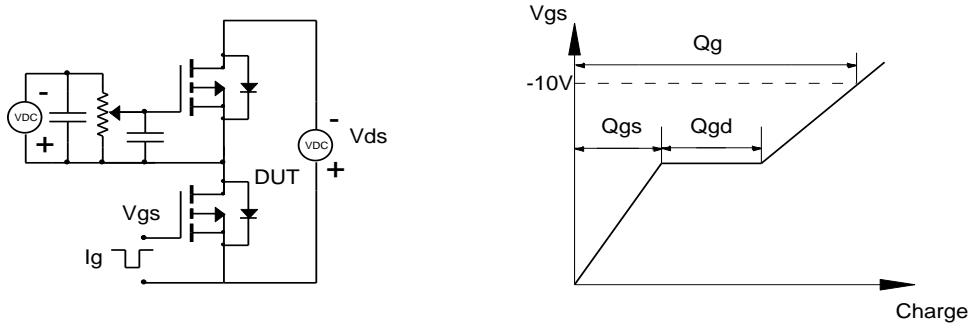
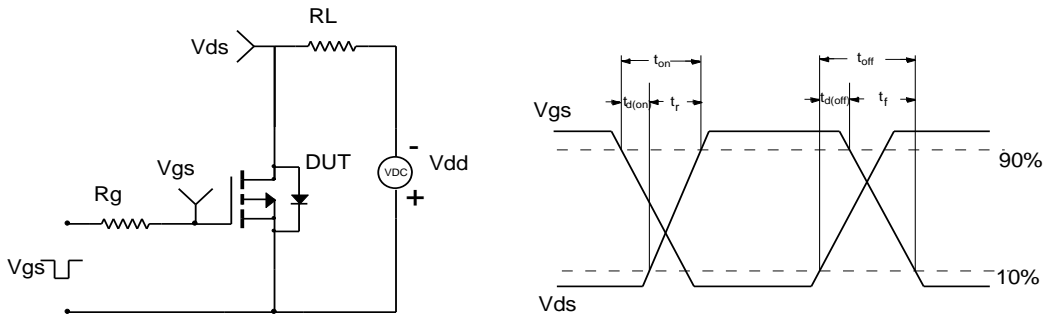


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

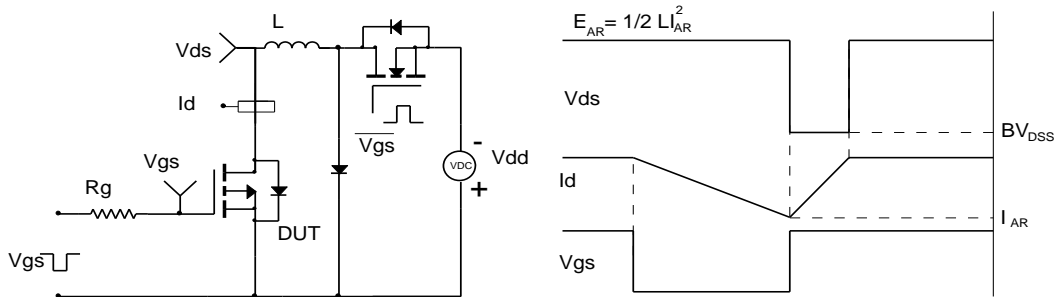
Gate Charge Test Circuit & Waveform



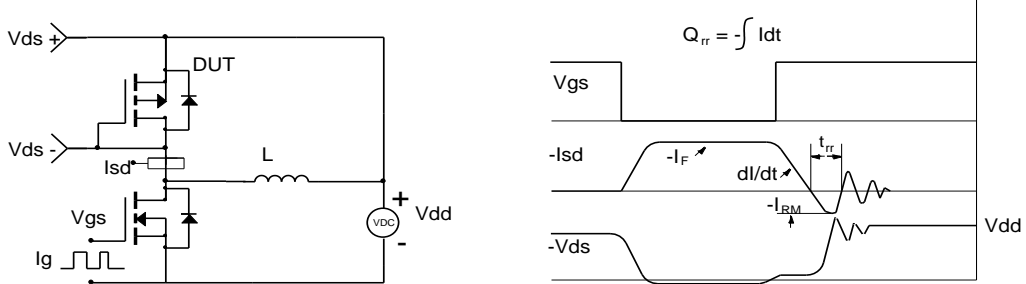
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



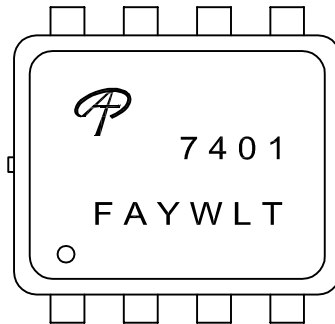
Diode Recovery Test Circuit & Waveforms





Document No.	PD-00873
Version	B
Title	AON7401 Marking Description

DFN3X3 PACKAGE MARKING DESCRIPTION



Green product

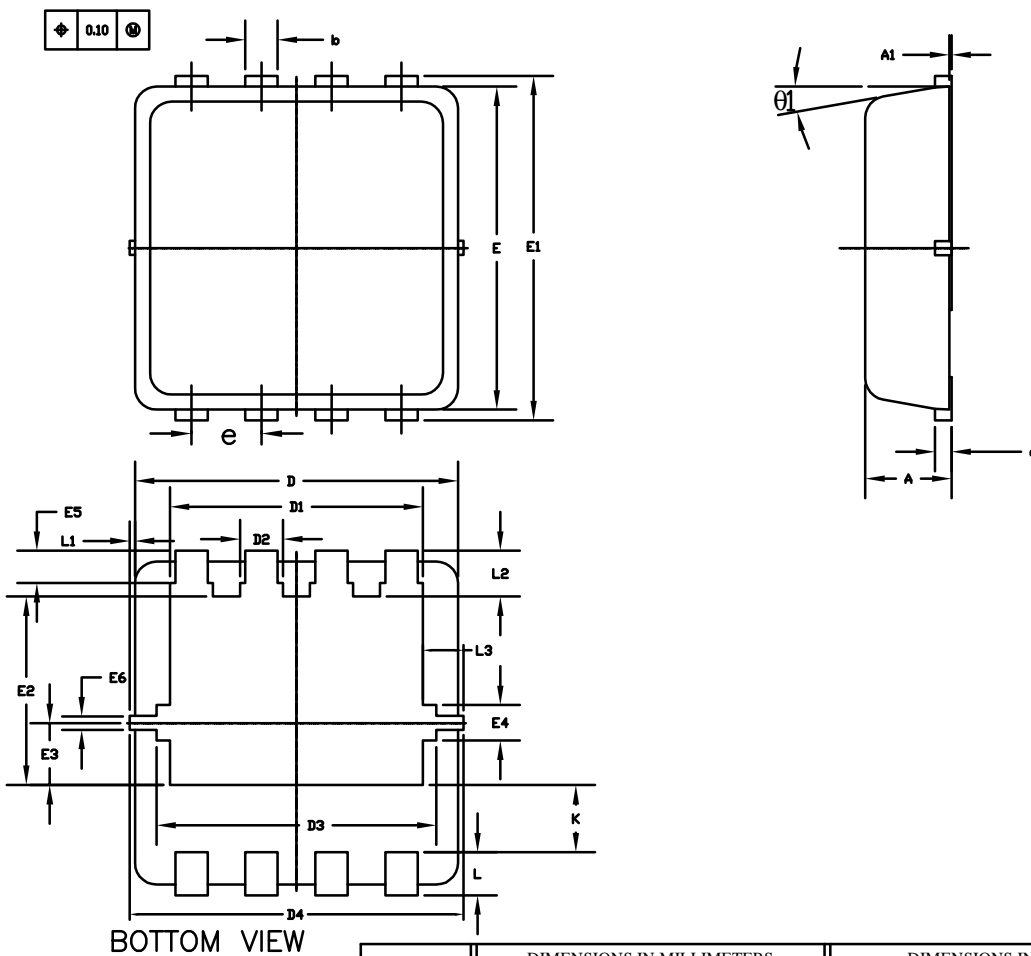
NOTE:

- LOGO - AOS Logo
- 7401 - Part number code
- F - Fab code
- A - Assembly location code
- Y - Year code
- W - Week code
- L&T - Assembly lot code

PART NO.	DESCRIPTION	CODE
AON7401	Green product	7401
AON7401L	Green product	7401

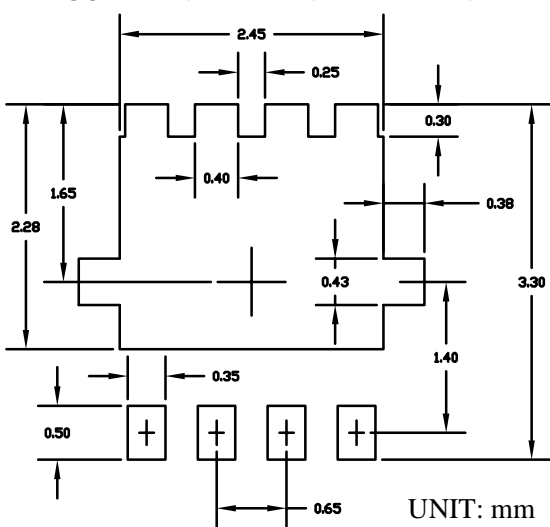


DFN3x3A_8L_EP1_P PACKAGE OUTLINE



BOTTOM VIEW

RECOMMENDED LAND PATTERN



UNIT: mm

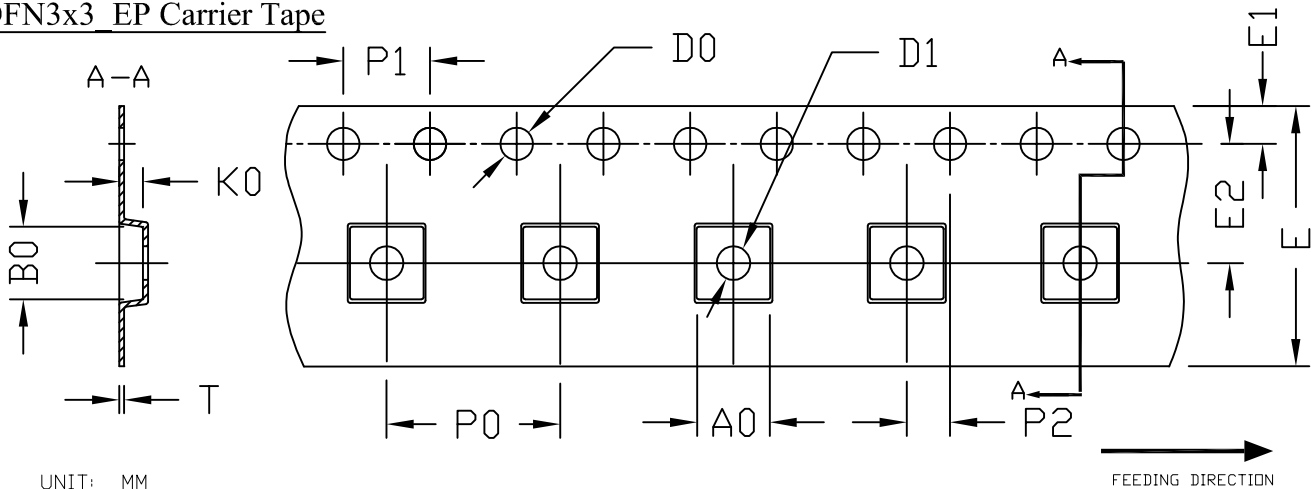
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A1	0.00	0.025	0.05	0.000	0.001	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
D1	2.25	2.35	2.45	0.089	0.093	0.097
D2	0.30	0.40	0.50	0.012	0.016	0.020
D3	2.50	2.60	2.70	0.098	0.102	0.106
D4	3.00	3.10	3.20	0.118	0.122	0.126
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	3.10	3.20	3.30	0.122	0.126	0.130
E2	1.65	1.75	1.85	0.065	0.069	0.073
E3	0.48	0.58	0.68	0.019	0.023	0.027
E4	0.23	0.33	0.43	0.009	0.013	0.017
E5	0.20	0.30	0.40	0.008	0.012	0.016
E6	0.075	0.125	0.175	0.003	0.005	0.007
e	0.60	0.65	0.70	0.024	0.026	0.028
K	0.52	0.62	0.72	0.020	0.024	0.028
L	0.30	0.40	0.50	0.012	0.016	0.020
L1	0	0.05	0.10	0	0.002	0.004
L2	0.33	0.43	0.53	0.013	0.017	0.021
L3	0.275	0.375	0.475	0.011	0.015	0.019
theta1	0°	10°	12°	0°	10°	12°

NOTE

1. PACKAGE DIMENSION IS EXCLUSIVE OF MOLD GATE BURR
2. PACKAGE DIMENSION IS EXCLUSIVE OF MOLD FLASH AND CUTTING BURR
3. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



DFN3x3 EP Carrier Tape

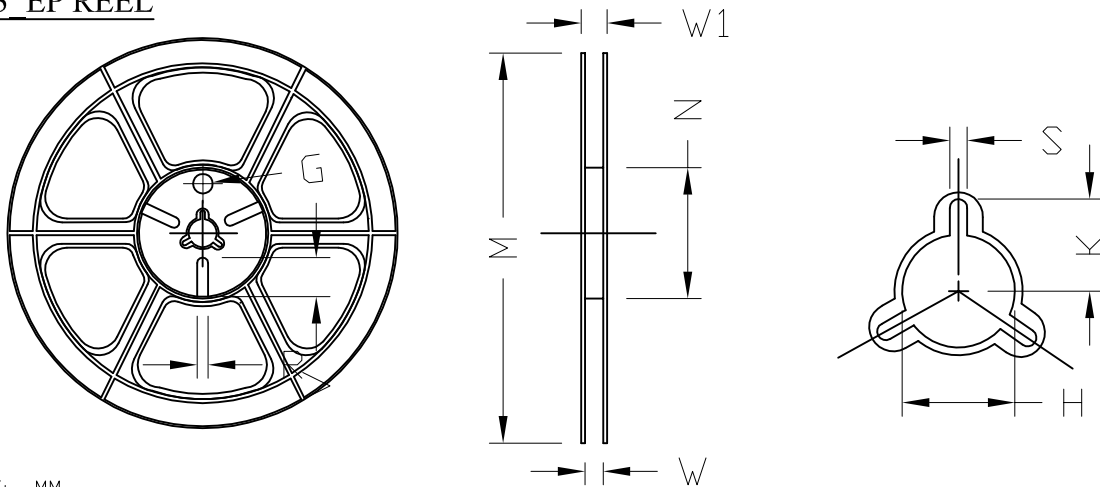


UNIT: MM

FEEDING DIRECTION

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
DFN3x3_EP	3.40 ±0.10	3.35 ±0.10	1.10 ±0.10	1.50 +0.10 -0	1.50 +0.10 -0	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.30 ±0.05

DFN3x3 EP REEL



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	∅330	∅330.00 ±0.50	∅97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	∅13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

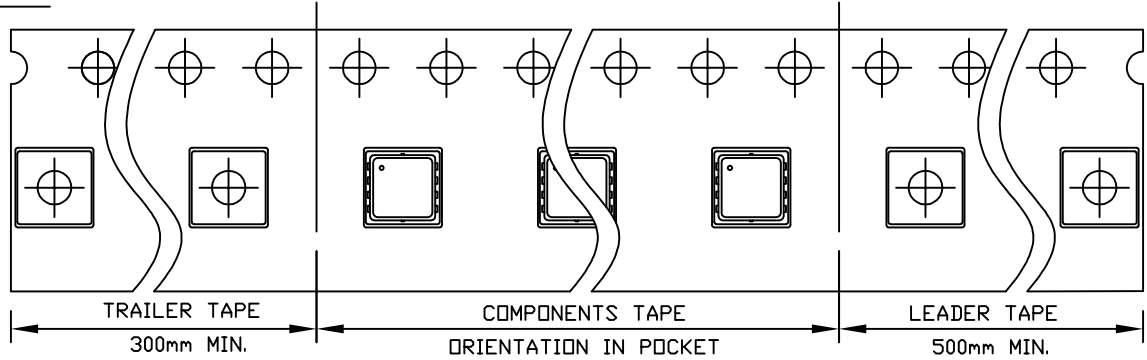


DFN3x3 EP TAPE

Leader / Trailer
& Orientation

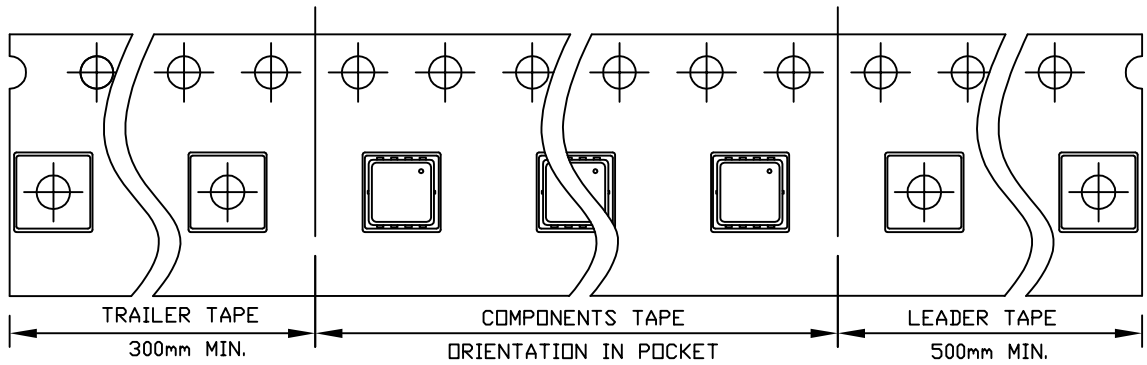
MOS

Unit Per Reel:
5000pcs



PIC

Unit Per Reel:
5000pcs





AOS Semiconductor

Product Reliability Report

AON7401, rev C

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com

This AOS product reliability report summarizes the qualification result for AON7401. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AON7401 passes AOS quality and reliability requirements.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation

I. Product Description:

The AON7401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

- RoHS Compliant
- Halogen-Free

Detailed information refers to datasheet.

II. Die / Package Information:

	AON7401
Process	Standard sub-micron Low voltage P channel
Package Type	DFN 3x3A
Lead Frame	Cu
Die Attach	Ag epoxy
Bonding	Cu wire
Mold Material	Epoxy resin with silica filler
MSL (moisture sensitive level)	Level 1 based on J-STD-020

Note * based on information provided by assembler and mold compound supplier

III. Result of Reliability Stress for AON7401

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	Standard
MSL Precondition	168hr 85°C /85%RH +3 cycle reflow@260°C	-	11 lots	2299pcs	0	JESD22-A113
HTGB	Temp = 150 °c, Vgs=100% of Vgsmax	168hrs 500hrs 1000 hrs	1 lot 3 lots (Note A*)	308pcs 77pcs / lot	0	JESD22-A108
HTRB	Temp = 150 °c, Vds=80% of Vdsmax	168hrs 500hrs 1000 hrs	1 lot 3 lots (Note A*)	308pcs 77pcs / lot	0	JESD22-A108
HAST	130°C, 85%RH, 33.3 psi, Vgs = 100% of Vgs max	100 hrs	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A110
Pressure Pot	121°C, 29.7psi, RH=100%	96 hrs	11 lots (Note A*)	847pcs 77pcs / lot	0	JESD22-A102
Temperature Cycle	-65°C to 150°C, air to air	250 / 500 cycles	11 lots (Note A*)	847pcs 77pcs / lot	0	JESD22-A104

Note A: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 7

MTTF = 15704 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AON7401). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2 \times (2 \times 77 \times 168 + 6 \times 77 \times 1000) \times 258] = 7$$

$$\text{MTTF} = 10^9 / \text{FIT} = 1.38 \times 10^8 \text{hrs} = 15704 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

K = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K

单击下面可查看定价，库存，交付和生命周期等信息

[>>AOS\(万代\)](#)